INFRA-RED Item No.: 120214

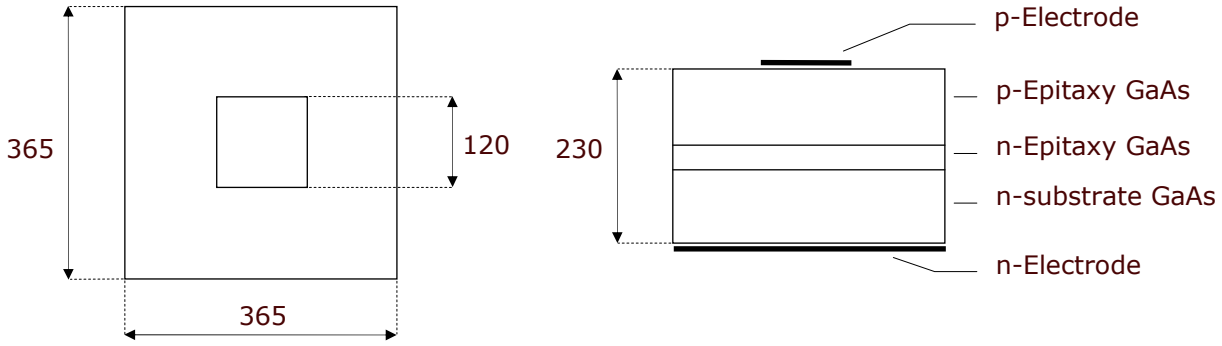
1. This specification applies to GaAs / GaAs LED Chips

2. Structure

2.1 Mesa structure

2.2 Electrodes p-side (anode) Au alloy
n-side (cathode) Au alloy

3. Outlines (dimensions in microns)



Wire bond contacts can also have a spider shape

4. Electrical and optical characteristics (T=25°C)

Parameter	*Symbol*	*Conditions*	*min*	*typ*	*max*	*Unit*
Forward voltage	V_F	I_F = 20 mA		1,20	1,40	V
Reverse current	I_R	V_R = 5 V			10	µA
output Power *	Φ_e	I_F = 20 mA	0,6	0,8		mW
		I_F = 50 mA	1,5	2,0		
Switching time	t_r, t_f	I_F = 100 mA		0,6		µs
Peak wavelength	λ_P	I_F = 20 mA		930		nm

* On request, wafers will be delivered according to output power classes
Power measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top
2) back contact on top

6. Labeling

Type	Lot No.	Φ_e typ min max	Quantity

© 2004

OSA Opto Light GmbH · Tel. +49-(0)30-65 76 26 83 · Fax +49-(0)30-65 76 26 81 · contact@osa-opto.com